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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/768,160	02/02/2004	Atsushi Kurokawa		6034
24956 7:	590 05/27/2004		EXAMINER	
MATTINGLY	Y, STANGER & MAL	MOTTOLA,	MOTTOLA, STEVEN J	
1800 DIAGON SUITE 370	IAL ROAD		ART UNIT	PAPER NUMBER
ALEXANDRIA	A, VA 22314		2817	· · · · · · · · · · · · · · · · · · ·

DATE MAILED: 05/27/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	Application No.		B K			
Office Action Summany	10/768,160	KUROKAWA ET AL.				
Office Action Summary	Examiner	Art Unit				
	Steven J. Mottola	2817				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence addre	9SS			
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period was realized to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	86(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days fill apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONEI	ely filed s will be considered timely. the mailing date of this comn O (35 U.S.C. § 133).	nunication,			
Status						
1) Responsive to communication(s) filed on						
,	action is non-final.					
•						
Disposition of Claims						
4) ☐ Claim(s) 15-34 is/are pending in the application 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 15-17,20-27,29-32 is/are rejected. 7) ☐ Claim(s) 18,19 and 28 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or	vn from consideration.					
Application Papers						
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) acce Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct	epted or b) objected to by the Edrawing(s) be held in abeyance. See	37 CFR 1.85(a).	1.121(d).			
11)☐ The oath or declaration is objected to by the Ex	aminer. Note the attached Office	Action or form PTO	-152.			
Priority under 35 U.S.C. § 119	•					
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Application rity documents have been received a (PCT Rule 17.2(a)).	on No ed in this National St	age			
Attachment(s)						
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ite	52)			

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The disclosure is objected to because of the following informalities: the specification should be updated at page one to reflect the current status of the parent application.

Appropriate correction is required.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 15,17,20,21,23-27,29,30,32-34 are rejected under 35 U.S.C. 103(a) as being unpatentable over Griffin et al.

Independent claims 15 and 26 will be treated first. Griffin et al. disclose in fig. 10 for instance an FET having a MES gate g so that the transistor may be read as the claimed MESFET. Note also that the device is referred to by Griffin et al. as a MESFET structure at col. 5, lines 59-60. It is formed so as to have a Schottky barrier (col. 4, line

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50) as claimed, forward gate current by increasing the gate bias voltage being inherent in such an arrangement (but also see col. 3, lines 44-46 of Griffin et al.) and a gate bias voltage supplied by a source Vgg and inductor L12 which may be read as the bias circuit claimed, the MES gate receiving a signal RF INPUT to be amplified superposed with the bias voltage as claimed, the difference between the claims and Griffin et al. being the specific bias voltage range claimed, greater than or equal to >65 volts, while Griffin et al. do not specify a certain voltage. However, it would have been obvious to set the gate bias Vgg to bias the transistor according to the desired transistor characteristics such as breakdown voltage and channel current because Griffin et al. have suggested just this at col. 7, lines 17-20. Regarding claims 17 & 27, the applicant has stated that a direct transition type of material includes GaAs; this is the material preferably used by Griffin et al. (see col. 4, lines 35-36). Regarding claims 20-21 and 29-30, see lines 51-55 of col. 4 of Griffin et al.; at least some of the materials listed (such as titanium-tungsten) should have a work function as claimed. Regarding claims 23-25 and 32-34, the MESFET may be integrated with or separately from other components; see col. 8, lines 31-41 of Griffin et al. Note the matching circuits in figs. 10 & 13.

Claim 16 is rejected under 35 U.S.C. 103(a) as being unpatentable over Griffin et al. in view of Peczalski.

The difference added by this claim is that the MESFET is stated to be enhancement or shallow depression type; this is not explicitly stated by Griffin et al. However, even if Griffin et al. prefer depletion mode, it would have been obvious to

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substitute enhancement mode MESFETs because Peczalski has taught just such a substitution at col. 7, lines 21-35. The overall device is MESFET power amp utilizing the Schottky barrier effect (col. 5, line 67) so that the teaching is from analogous art.

Claims 22 and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Griffin et al. in view of Smith.

The difference added by these claims is the specification of platinum or palladium as a gate electrode material; however, the use of such a material in the MESFET of Griffin et al. would have been obvious as Smith disclose the use of platinum in the context of a MESFET with a Schottky barrier at col. 18, lines 42-51.

Claims 18,19 and 28 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The gate bias circuit ripple filtering capacitor of these claims is not disclosed in the context claimed in the prior art of record.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven J. Mottola whose telephone number is 571-272-1766. The examiner can normally be reached on M-Th from 8 to 5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Robert J. Pascal, can be reached on 571-272-1769. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for

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published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only.

For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Steven J. Mottola Primary Examiner